



DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)}	Package	I _D T _A = +25°C
60V	6Ω @ V _{GS} = 5V	SOT363	90mA
000	5Ω @ V _{GS} = 10V	301303	115mA

Description

This new generation MOSFET has been designed to minimize the on-state resistance (RDS(ON)) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

Load Switch

Features and Benefits

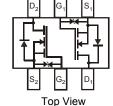
- **Dual N-Channel MOSFET**
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- ESD Protected Gate, 1KV (HBM)
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Alloy 42 leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208 @3
- Terminal Connections: See Diagram
- Weight: 0.006 grams (approximate)







Internal Schematic

Top View

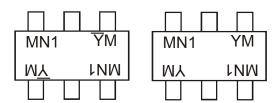
Ordering Information (Note 4)

Part Number	Case	Packaging		
DMN66D0LDW-7	SOT363	3,000/Tape & Reel		

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + CI) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



MN1= Product Type Marking Code YM = Date Code Marking for SAT (Shanghai Assembly/ Test site) YM = Date Code Marking for CAT (Chengdu Assembly/ Test site) Y or \overline{Y} = Year (ex: A = 2013) M = Month (ex: 9 = September)

Date Code Key

Year	2007	2008	2009	2010	201	1	2012	2	013	2014	2015	2016	2017
Code	U	V	W	Х	Y		Z		Α	В	С	D	Е
			·				- 1 .		_	<u> </u>		1	
Month	Jan	Feb	Mar	Apr	May	Ju	ın J	ul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	3	7	8	9	0	N	D

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Drain-Source Voltage		V_{DSS}	60	V
Gate-Source Voltage (Note 5)	Continuous	V_{GSS}	±20	V
Drain Current (Note 5)	Continuous Continuous @ +100°C Pulsed	I _D	115 73 800	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation Derating above $T_A = +25^{\circ}C$ (Note 5)	P _D	250 1.6	mW mW/°C
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	500	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C

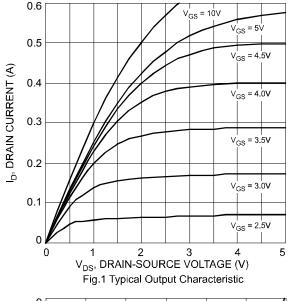
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic			Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)					•	•	
Drain-Source Breakdown Voltage		BV _{DSS}	60	70	_	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	@ T _C = +25°C @ T _C = +125°C	I _{DSS}	_	_	1.0 500	μA	V _{DS} = 60V, V _{GS} = 0V
Gate-Body Leakage		I _{GSS}	_	_	±5	μА	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage		V _{GS(th)}	1.2		2.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance	@ T _J = +25°C	R _{DS (ON)}	_	3.5	6	Ω	V _{GS} = 5.0V, I _D = 0.115A
	@ T _J = +125°C			3.0	5		V _{GS} = 10V, I _D = 0.115A
Forward Transconductance		9 FS	80	VsD	_	mS	V _{DS} = 10V, I _D = 0.115
Diode Forward Voltage		V _{SD}	_	0.8	1.2	V	V _{GS} = 0V, I _S = 115mA
DYNAMIC CHARACTERISTICS							
Input Capacitance		C _{iss}	_	23	_	pF	
Output Capacitance		Coss	_	3.4	_	pF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$
Reverse Transfer Capacitance		Crss	_	1.4	_	pF	
SWITCHING CHARACTERISTICS							
Turn-On Delay Time		t _{D(ON)}	_	10	_	ns	$V_{DD} = 30V$, $I_D = 0.115A$, $R_L = 150\Omega$,
Turn-Off Delay Time		t _{D(OFF)}	_	33	_	ns	$V_{GEN} = 10V_{,} R_{GEN} = 25\Omega$

Notes:

^{5.} Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com.6. Short duration pulse test used to minimize self-heating effect.





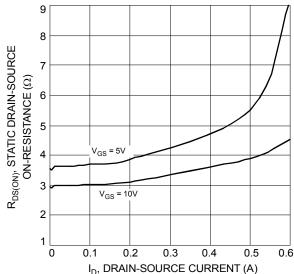


Fig. 3 On-Resistance vs. Drain Current & Gate Voltage

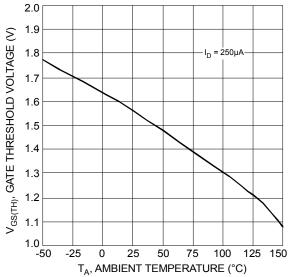
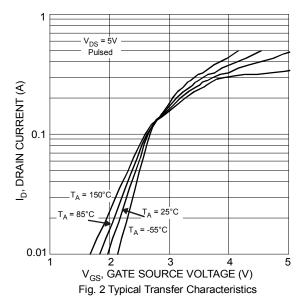


Fig. 5 Gate Threshold Variation vs. Ambient Temperature



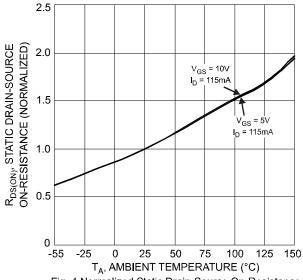
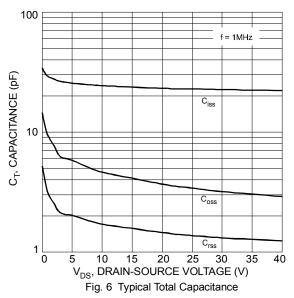


Fig. 4 Normalized Static Drain-Source On-Resistance vs. Ambient Temperature





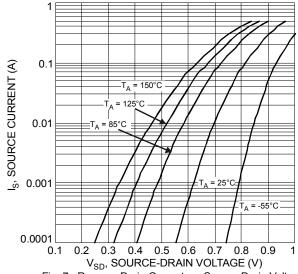
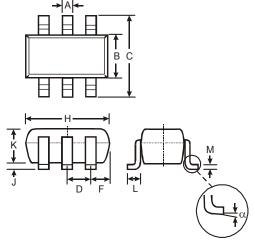


Fig. 7 Reverse Drain Current vs. Source-Drain Voltage

Package Outline Dimensions

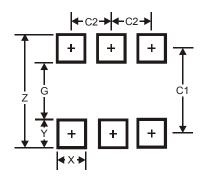
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT363						
Dim	Min	Max				
Α	0.10	0.30				
В	1.15	1.35				
С	2.00	2.20				
D	0.65 Typ					
F	0.40	0.45				
Η	1.80	2.20				
J	0	0.10				
K	0.90 1.00					
L	0.25	0.40				
М	0.10	0.22				
α	0°	8°				
All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.5
G	1.3
Х	0.42
Υ	0.6
C1	1.9
C2	0.65



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